

描述 / Descriptions

TO-247 塑封封装绝缘栅双极晶体管。 Insulated-Gate Bipolar Transistor in a TO-247 Plastic Package.

特征 / Features

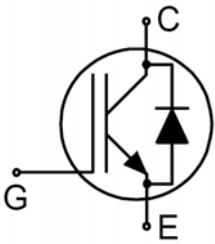
低栅极电荷、正温度系数、低饱和压降、RoHS 产品。

Low gate charge, Low saturation voltage, Positive temperature coefficient, RoHS product.

用途 / Applications

逆变器、变频器、电磁炉、不间断电源。

General purpose inverter, Frequency converters, Induction Heating(IH), Uninterrupted Power Supply(UPS).

内部等效电路 / Equivalent Circuit**引脚排列 / Pinning**

PIN1 : Gate

PIN 2 : Collector

PIN 3 : Emitter

放大及印章代码 / h_{FE} Classifications & Marking

见印章说明。 See Marking Instructions.

极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector-emitter voltage	V_{CES}	1200	V
Gate-emitter voltage	V_{GES}	±20	V
Collector current	I_C	50	A
Collector current@ $T_C=100^\circ\text{C}$		25	A
Collector peak current, T_P limited by T_{JMAX}	I_{CM}	60	A
Diode forward current@ $T_C=100^\circ\text{C}$	I_F	25	A
Diode maximum forward current	I_{FM}	75	A
Power dissipation($T_C=25^\circ\text{C}$)	P_D	350	W
Operating junction and storage temperature range	T_J, T_{stg}	-55~150	°C
Maximum temperature for soldering	T_L	300	°C
IGBT thermal resistance,junction-case	$R_{th(j-c)}$	0.4	°C/W
Diode thermal resistance,junction-case	$R_{th(j-c)}$	2	°C/W
Thermal resistance,junction-ambient	$R_{th(j-a)}$	40	°C/W

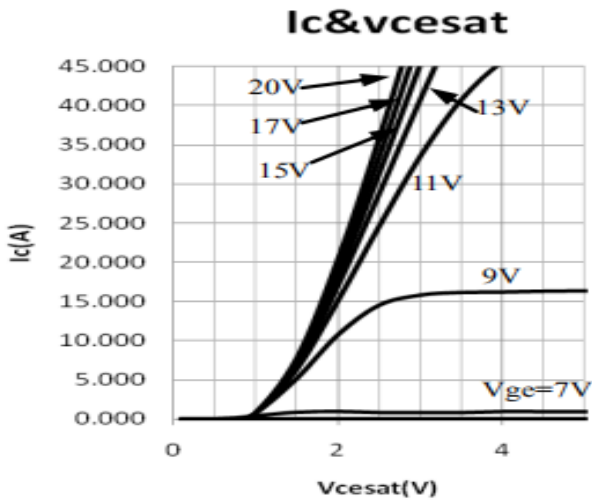
电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector-emitter breakdown voltage	V_{CES}	$V_{GE}=0V$ $I_{CE}=250\mu A$	1200	-	-	V
Breakdown Voltage Temperature Coefficient	$\frac{\Delta BV_{CES}}{\Delta T_J}$	$I_{CE}=1mA$;reference to 25°C		0.6		V/°C
Zero gate voltage Collector current	I_{CES}	$V_{GE}=0V$; $V_{CE}=1200V$ $T_c=25^\circ C$	-	-	0.2	mA
		$T_c=100^\circ C$			2	mA
		$T_c=150^\circ C$			2.5	mA
Gate-body leakage current	I_{GES}	$V_{GE}=\pm 20V$ $V_{CE}=0V$	-	-	± 100	nA
Gate threshold voltage	$V_{GE(th)}$	$I_C=600\mu A$ $V_{CE}=V_{GE}$	4.5	-	6.5	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=25A$; $V_{GE}=15V$ $T_c=25^\circ C$	-	1.8	2.45	V
		$T_c=100^\circ C$		2.0		V
		$T_c=150^\circ C$		2.1		V
Short Collector current	$I_{C(SC)}$	$V_{GE}=15V$; $V_{CE}=600V$; $t_{sc}<10\mu s$ $T_c=25^\circ C$		160		A
Input capacitance	C_{ies}	$V_{CE}=25V$ $V_{GE}=0V$ $f=1MHz$	-	1600	2400	pF
Output capacitance	C_{oes}		-	120	190	
Reverse transfer capacitance	C_{res}		-	84	130	

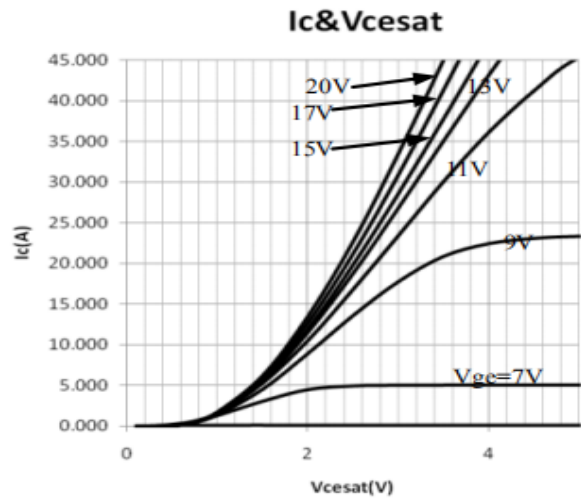
电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Turn-on delay time	$t_{d(ON)}$	$V_{CE}=600V$ $I_C=25A$ $R_G=10\Omega$ Inductive Load	-	90	-	ns
Rise time	t_r		-	75	-	
Turn-off delay time	$t_{d(OFF)}$		-	210	-	
Fall time	t_f		-	100	-	
Turn-On Switching Loss	E_{on}	$V_{CE}=600V$ $I_C=25A$ $V_{GE}=15V$	-	2.8	-	mJ
Turn-Off Switching Loss	E_{off}		-	1.1	-	
Total Switching Loss	E_{ts}		-	3.9	-	
Total gate charge	Q_G	$V_{CE}=600V$ $I_C=25A$ $V_{GE}=15V$	-	177	274	nC
Gate-emitter charge	Q_{G-E}		-	16	26	
Gate-collector charge	Q_{G-C}		-	61	94	
Diode forward voltage	V_F	$I_F=25A$	-	1.7	2.9	V
Reverse recovery time	T_{rr}	$V_{GE}=0V$, $V_R=800V$ $I_F=25A$	-	230		ns
Reverse recovery charge	Q_{rr}	$di/dt=200A/\mu S$	-	1200		nC

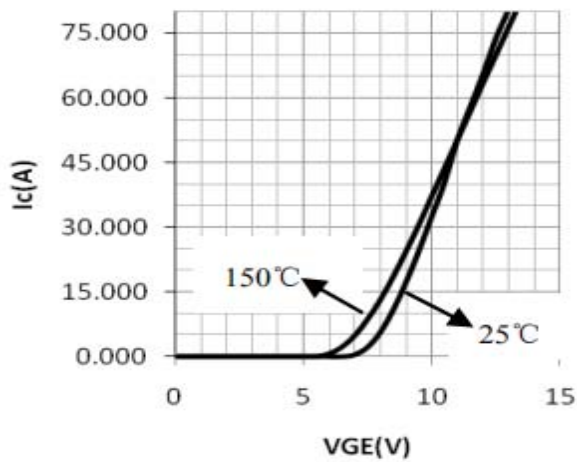
电参数曲线图 / Electrical Characteristic Curve



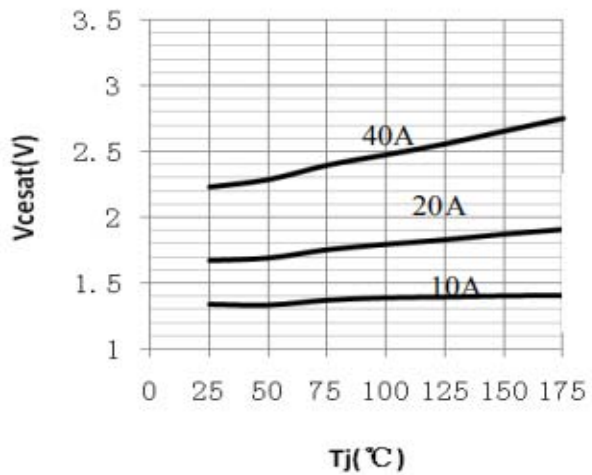
1. Typical Output Characteristics (Tj=25°C)



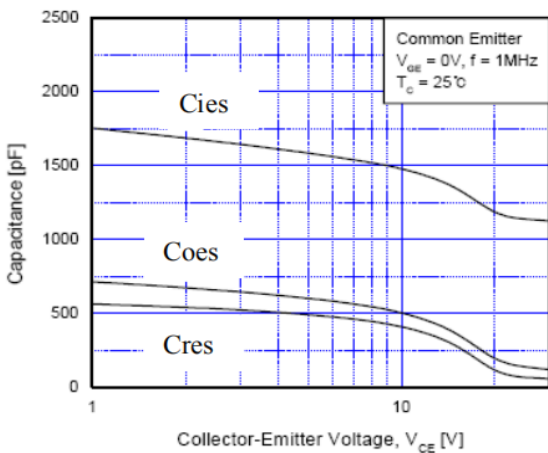
2. Typical Output Characteristics (Tj=150°C)



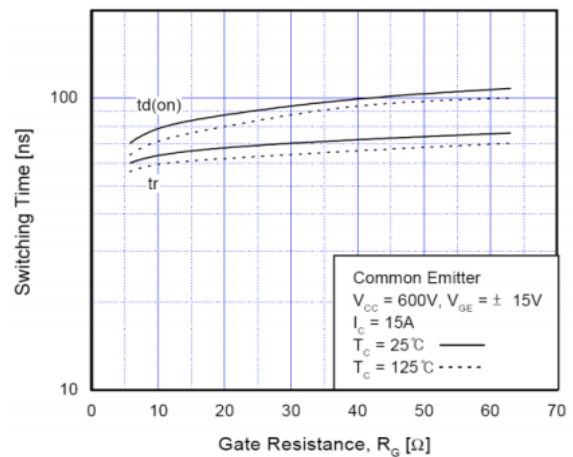
3. Typical Saturation Voltage Characteristics



4. Saturation Voltage vs. Case Temperature at Variant Current Level

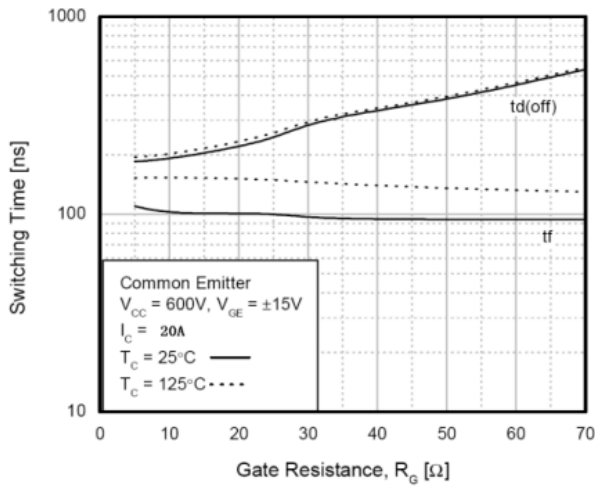


5. Capacitance Characteristics

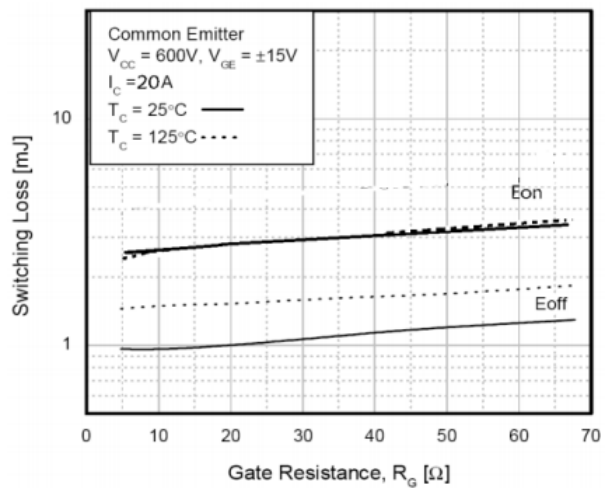


6. Turn-On Characteristics vs. Gate Resistance

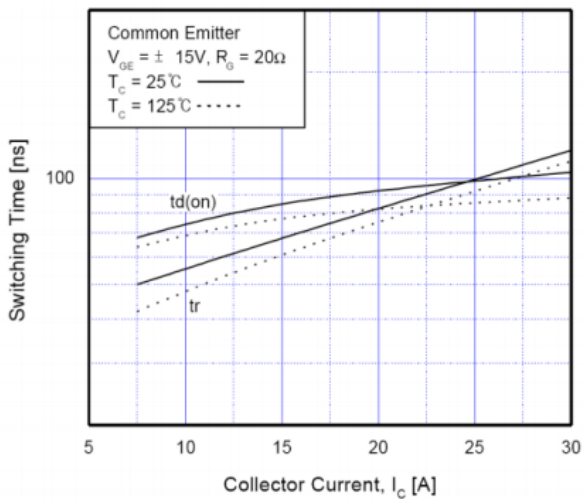
电参数曲线图 / Electrical Characteristic Curve



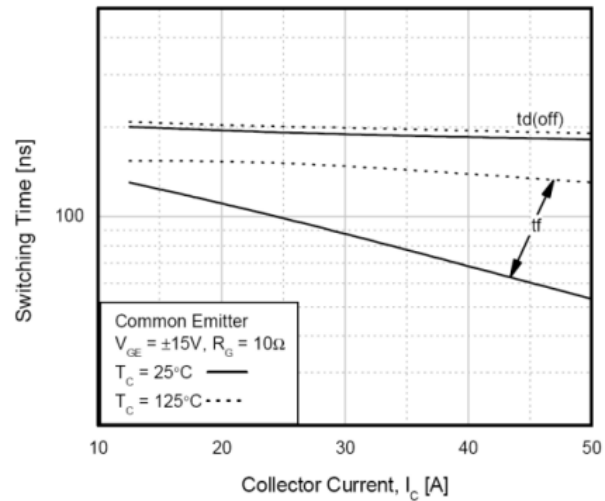
7. Turn-Off Characteristics vs. Gate Resistance



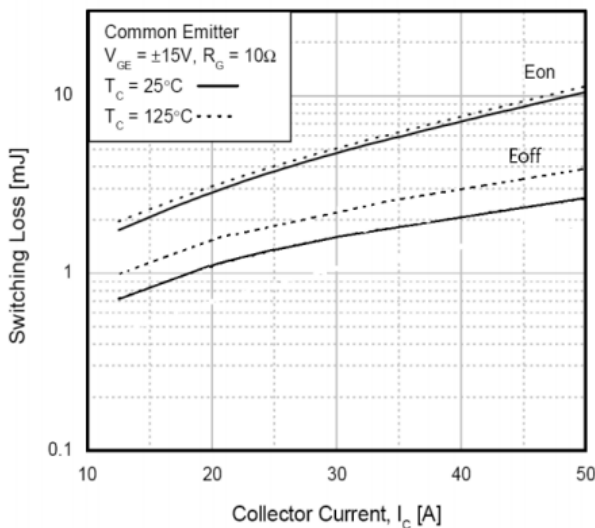
8. Switching Loss vs. Gate Resistance



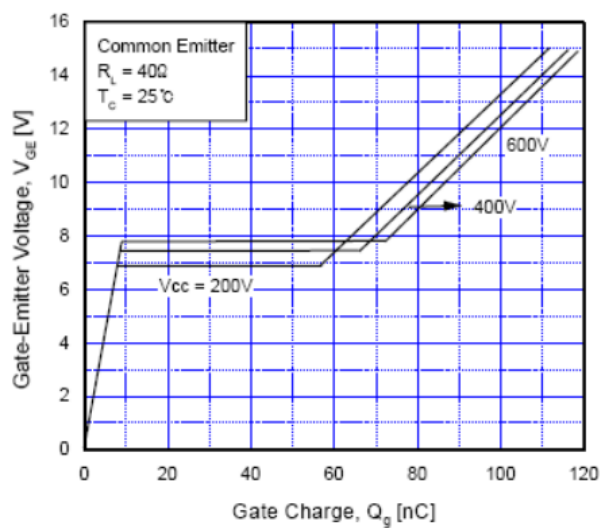
9. Turn-On Characteristics vs. Collector Current



10. Turn-Off Characteristics vs. Collector Current

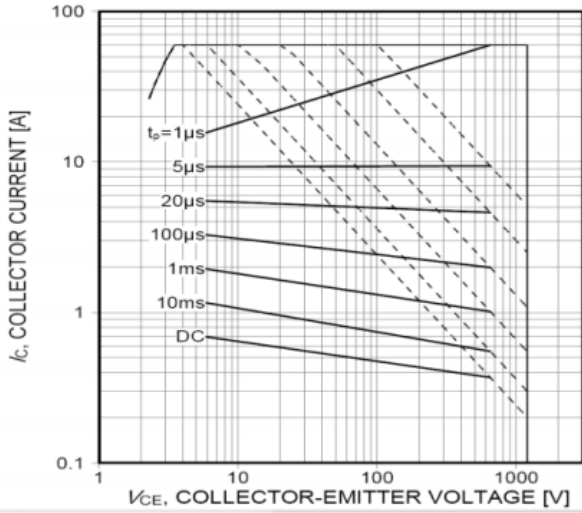


11. Switching Loss vs. Collector Current

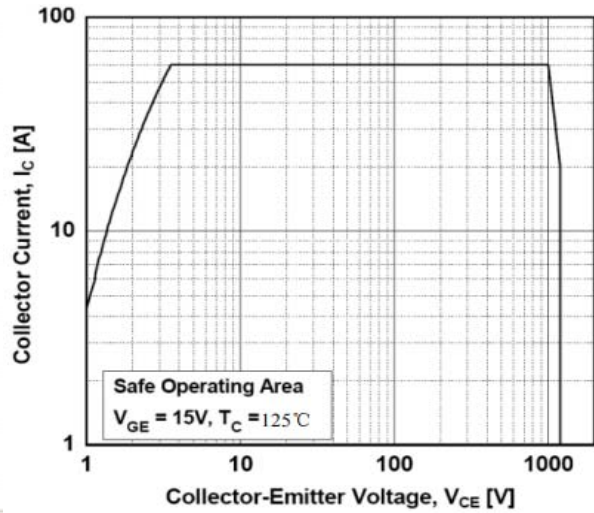


12. Gate Charge Characteristics

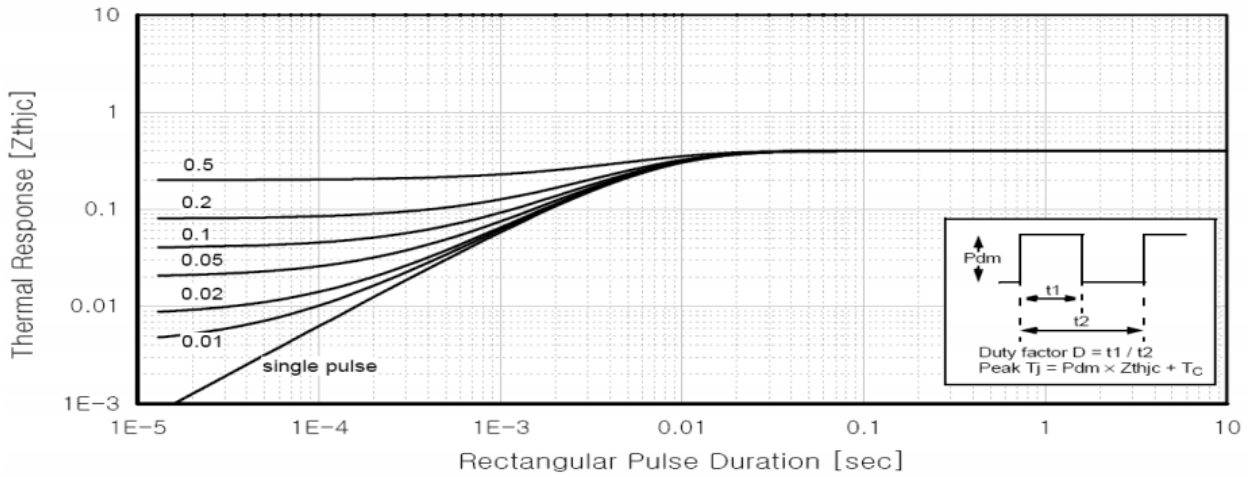
电参数曲线图 / Electrical Characteristic Curve



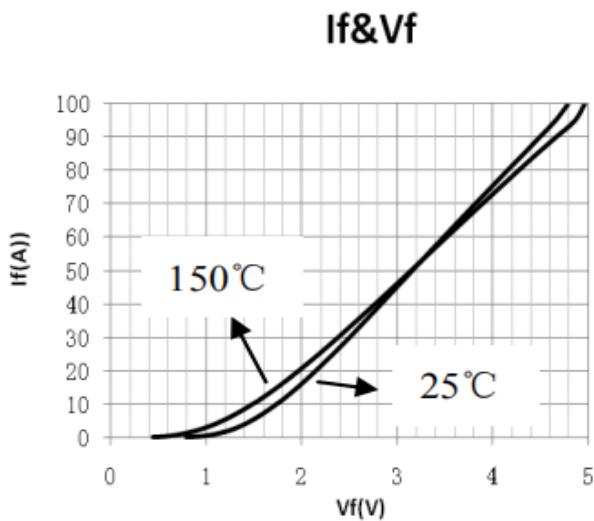
13.SOA Characteristics



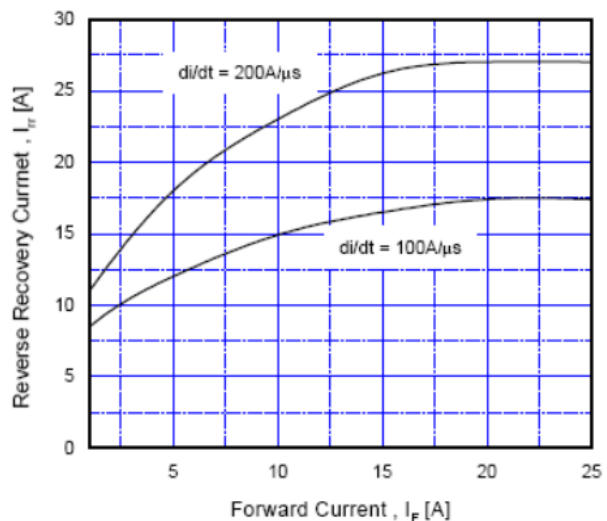
14.Turn-Off SOA



15.Transient Thermal Impedance

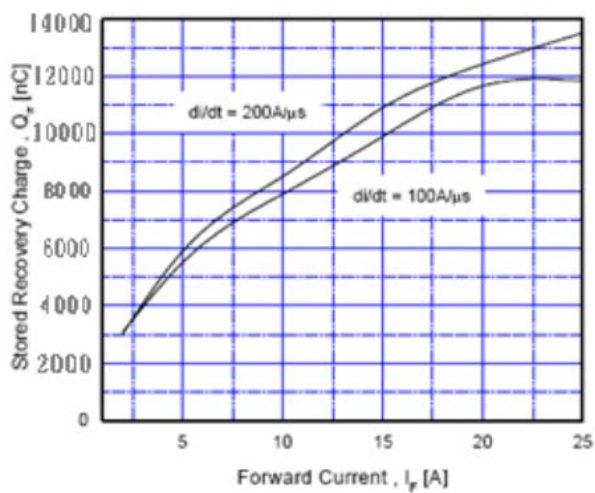


16.Forward Characteristics

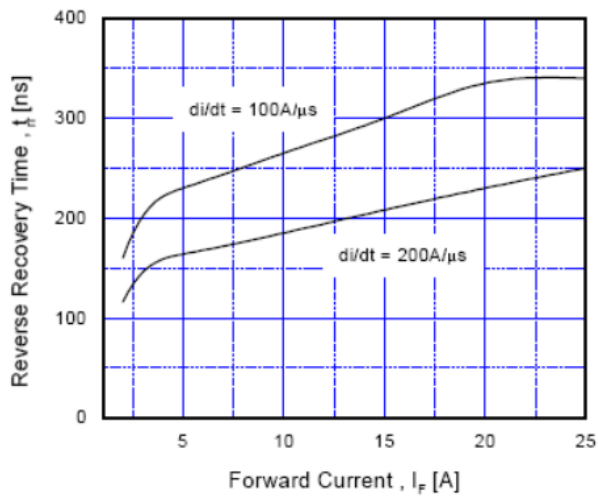


17.Reverse Recovery Current

电参数曲线图 / Electrical Characteristic Curve

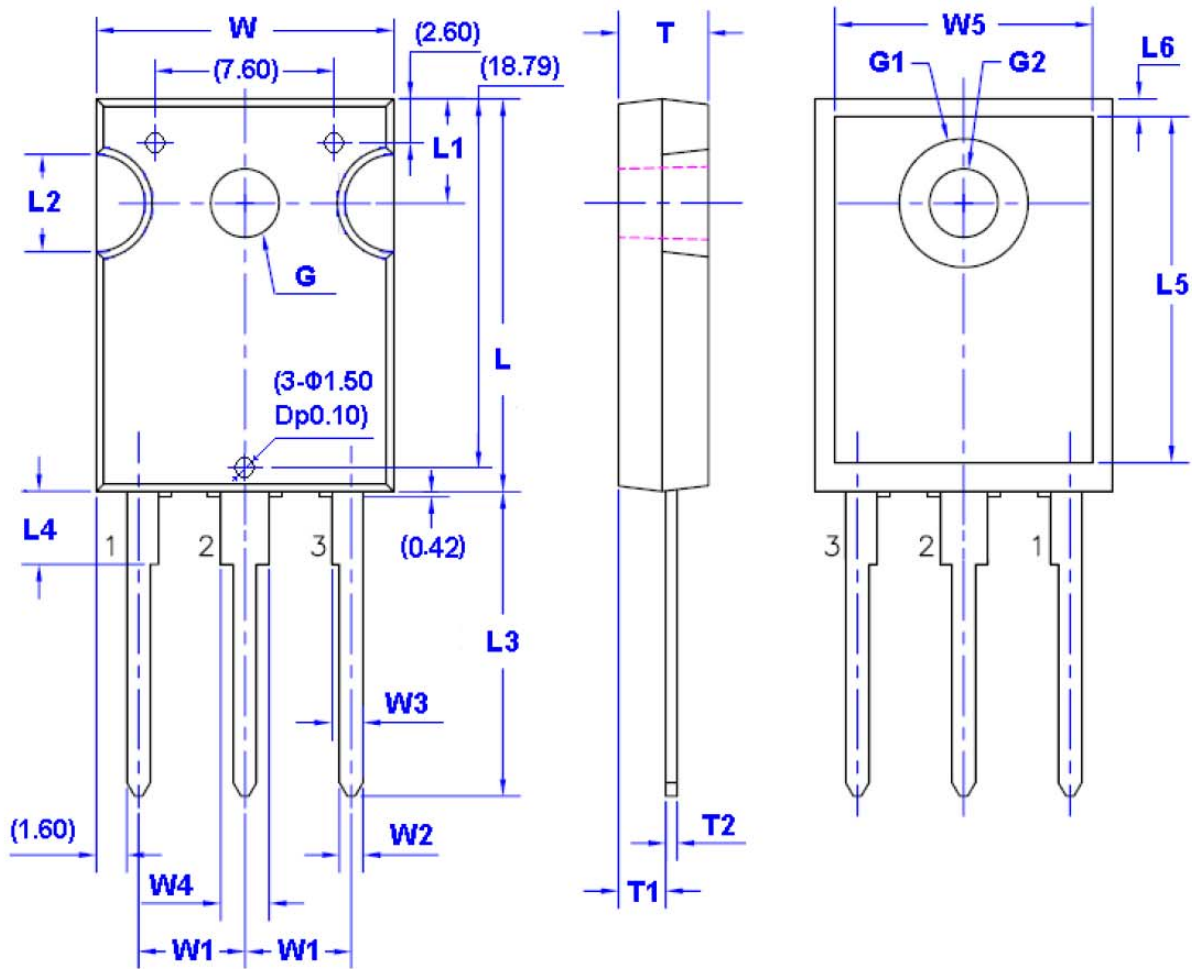


18.Stored Charge



19.Reverse Recovery Time

外形尺寸图 / Package Dimensions

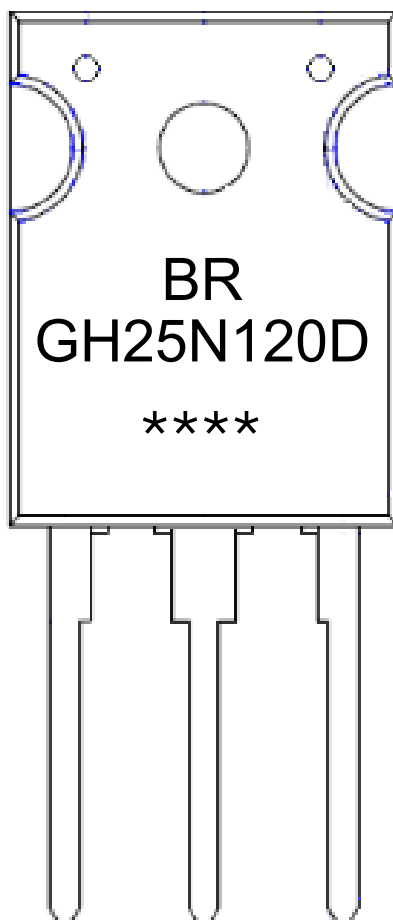


(单位: mm)

符号	尺寸		符号	尺寸		符号	尺寸		符号	尺寸	
	Min	Max		Min	Max		Min	Max		Min	Max
W	15.37	15.87	W5	12.81	--	L4	3.69	3.93	T2	0.51	0.71
W1	5.56 (TYP)		L	20.32	20.82	L5	13.08	--	G(Φ)	3.51	3.65
W2	1.17	1.35	L1	5.34	5.58	L6	0.51	1.35	G1(Φ)	6.61	6.85
W3	1.53	1.77	L2	4.96	5.20	T	4.58	4.82	G2(Φ)	3.51	3.65
W4	2.42	2.66	L3	15.75	16.25	T1	2.29	2.66			

注: () 内数值为参考值。尺寸不包含毛刺及模具溢料。

印章说明 / Marking Instructions



说明：

BR: 为公司代码

G25N120D : 为产品型号

**** : 为生产批号代码，随生产批号变化。

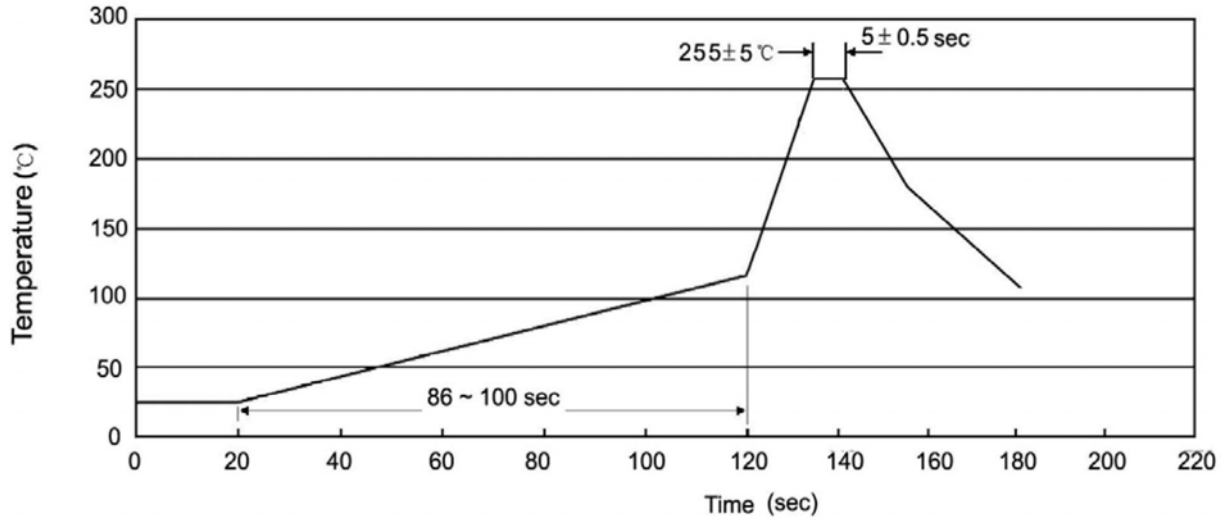
Note:

BR: Company Code.

G25N120D: Product Type.

****: Lot No. Code, code change with Lot No.

波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)



说明：

- 1、预热温度 25~150°C，时间 60~90sec;
- 2、峰值温度 255±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:255±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：270±5°C 时间：10±1 sec. Temp.:270±5°C Time:10±1 sec

包装规格 / Packaging SPEC.

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-247	30	15	450	5	2250	497.5×46×8	555×164×50	575×290×180

使用说明 / Notices